

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2902

DESCRIPTION

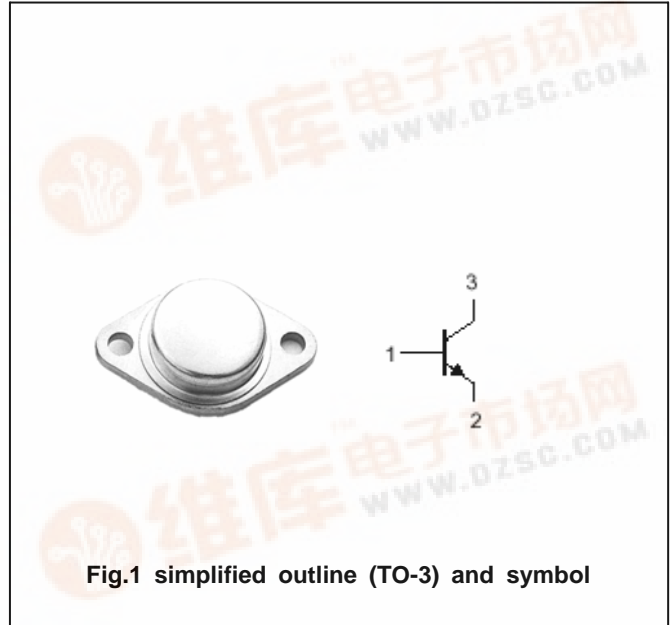
- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CBO}	Collector-base voltage	Open emitter	800	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	9	V
I _C	Collector current		15	A
I _{CM}	Collector current-Peak		30	A
P _C	Collector power dissipation	T _C =25°C	150	W
T _j	Junction temperature		200	°C
T _{stg}	Storage temperature		-65~200	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0; L=25mH	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	9			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =7.5A; I _B =2.5A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =7.5A; I _B =2.5A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =640V; I _E =0			50	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =9V; I _C =0			50	μ A
h _{FE}	DC current gain	I _C =7.5A ; V _{CE} =5V	10		35	

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PACKAGE OUTLINE

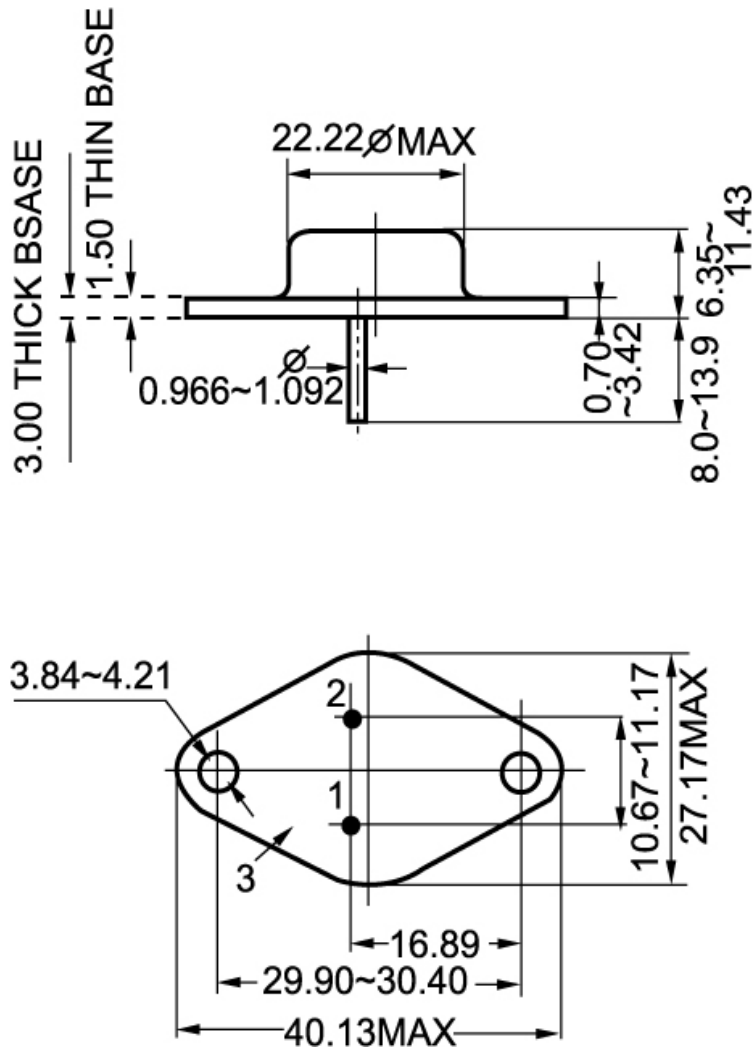


Fig.2 Outline dimensions